(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
29 July 2010 (29.07.2010)

PCT

(10) International Publication Number
WO 2010/085757 A1

(51) International Patent Classification:
H01L 21/8234 (2006.01) *H01L 21/8238* (2006.01)

(21) International Application Number:
PCT/US2010/021999

(22) International Filing Date:
25 January 2010 (25.01.2010)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
12/359,764 26 January 2009 (26.01.2009) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declarations under Rule 4.17:

— *as to the identity of the inventor (Rule 4.17(i))*

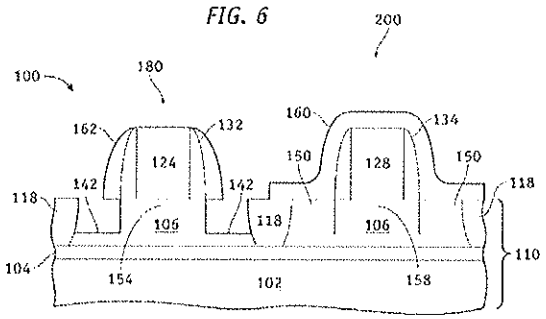
Published:

— *with international search report (Art. 21(3))*

— *with amended claims (Art. 19(1))*

(54) Title: METHODS FOR FABRICATING MOS DEVICES HAVING EPITAXIALLY GROWN STRESS-INDUCING SOURCE AND DRAIN REGIONS

FIG. 6



(57) Abstract: Methods of fabricating a semiconductor device (100) on and in a semiconductor substrate (110) having a first region (180) and a second region (200) are provided. In accordance with an exemplary embodiment of the invention, a method comprises forming a first gate stack (124) overlying the first region (180) and a second gate stack (128) overlying the second region (200), etching into the substrate (110) first recesses (142) and second recesses (142), the first recesses (142) aligned at least to the first gate stack (124) in the first region (180), and the second recesses (142) aligned at least to the second gate stack (128) in the second region (200), epitaxially growing a first stress-inducing monocrystalline material (150) in the first and second recesses (142), removing the first stress-inducing monocrystalline material (150) from the first recesses (142), and epitaxially growing a second stress-inducing monocrystalline material (170) in the first recesses (142), wherein the second stress-inducing monocrystalline material (170) has a composition different from the first stress-inducing monocrystalline material (150).

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